

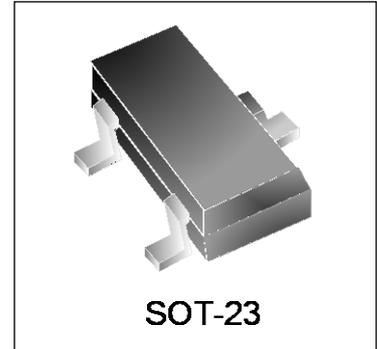


WM03P27M

P-Channel MOSFET

Features

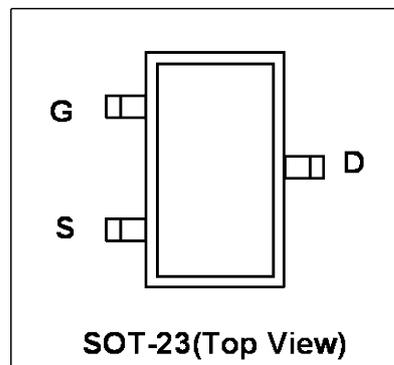
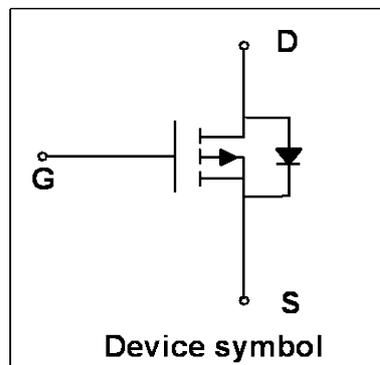
- $V_{DS} = -30V$, $I_D = -2.7A$
 $R_{DS(on)} < 88m\Omega$ @ $V_{GS} = -10V$
 $R_{DS(on)} < 138m\Omega$ @ $V_{GS} = -4.5V$
- High Dense Cell Design for Extremely Low $R_{DS(ON)}$
- Exceptional On-Resistance and Maximum DC Current Capability
- Fully Characterized Capacitance and Avalanche Voltage and Current



Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant

Schematic & PIN Configuration



Absolute Maximum Rating

Rating		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_A = 25^\circ C$	I_D	-2.7	A
Pulsed Drain Current		I_{DM}	-10.8	A
Power Dissipation	$T_A = 25^\circ C$	P_D	1.3	W
Operating Junction Temperature		T_J	150	$^\circ C$
Storage Temperature		T_{STG}	-55 to 150	$^\circ C$
Thermal Resistance from Junction to Ambient ²		$R_{\theta JA}$	96	$^\circ C/W$

Electrical Characteristics ($T_{amb}=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	μA
Gate-Source Leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
Gate-Source Threshold Voltage ³	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.5	-3	V
Drain-Source On-State Resistance ³	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-3.5A$	-	66	88	m Ω
		$V_{GS}=-4.5V, I_D=-2.5A$	-	88	138	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=-15V,$ $f=1.0MHz$	-	345	-	pF
Output Capacitance	C_{oss}		-	47	-	
Reverse Transfer Capacitance	C_{rss}		-	35	-	
Switching Characteristics						
Total Gate Charge ⁴	Q_g	$V_{GS}=-4.5V, V_{DS}=-15V,$ $I_D=-2.5A$	-	3.9	-	nC
Gate-Source Charge ⁴	Q_{gs}		-	1.1	-	
Gate-Drain Charge ⁴	Q_{gd}		-	1.5	-	
Turn-on Delay Time ⁴	$t_{d(on)}$	$V_{DD}=-15V, R_L=15\Omega,$ $V_{GEN}=-4.5V, I_D=-1A,$ $R_g=1\Omega$	-	36.8	-	ns
Rise Time ⁴	t_r		-	37	-	
Turn-off delay time ⁴	$t_{d(off)}$		-	28.2	-	
Fall Time ⁴	t_f		-	15.5	-	
Drain-Source Body Diode Characteristics						
Body Diode Voltage	V_{SD}	$I_S=-1.5A, V_{GS}=0V$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Guaranteed by design, not subject to product.

Typical Characteristics

Figure 1. Output Characteristics

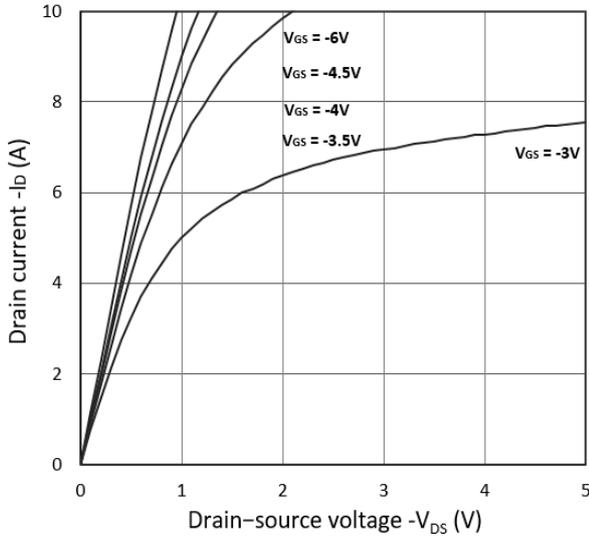


Figure 2. Transfer Characteristics

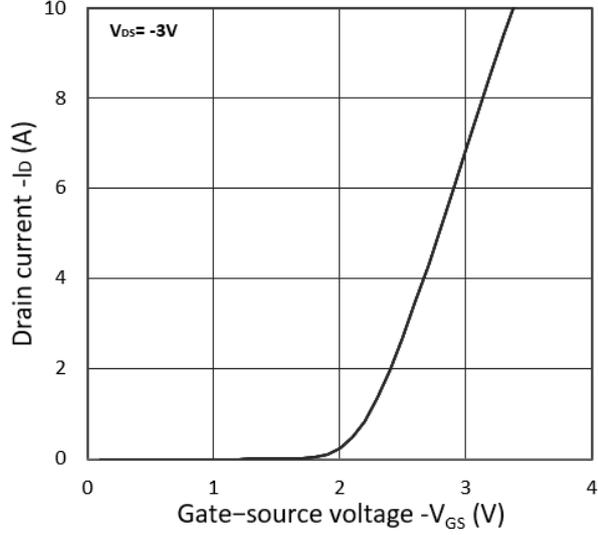


Figure 3. $R_{DS(on)}$ vs. I_D

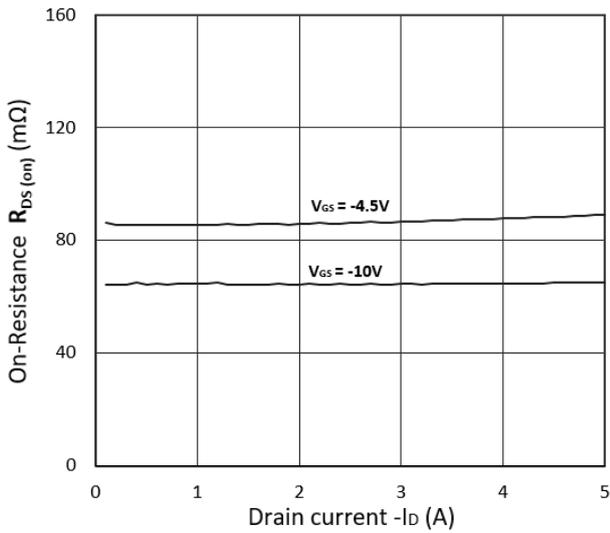


Figure 4. $R_{DS(on)}$ vs. V_{GS}

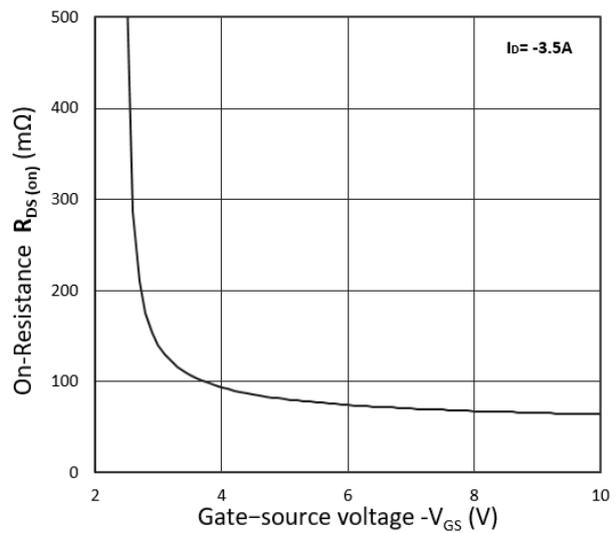


Figure 5. I_S vs. V_{SD}

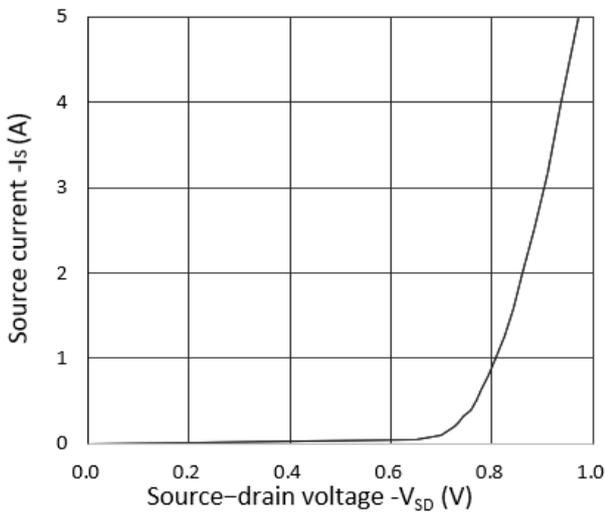
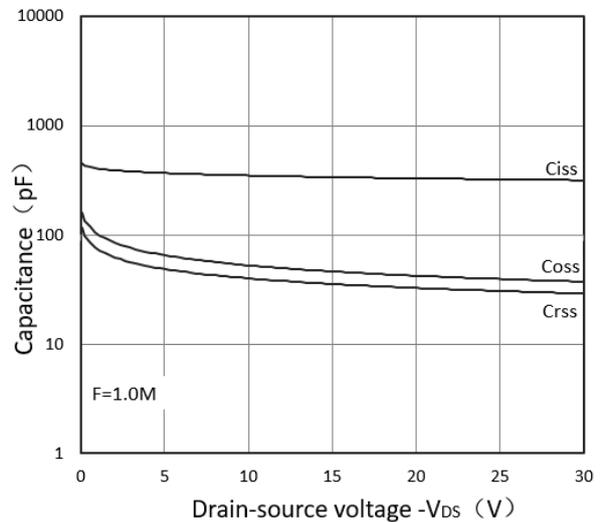


Figure 6. Capacitance Characteristics



Outline Drawing – SOT-23

PACKAGE OUTLINE

DIMENSIONS				
SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.15	0.035	0.045
A1	0.00	0.10	0.000	0.004
b	0.30	0.50	0.012	0.020
c	0.08	0.15	0.003	0.006
D	2.80	3.00	0.110	0.118
E	2.25	2.55	0.089	0.100
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 BSC	
e1	1.80	2.00	0.071	0.079
L	0.45	0.65	0.018	0.026
θ	0	8°	0	8°

DIMENSIONS		
DIM	INCHES	MILLIMETERS
M	0.080	2.02
C	0.032	0.80
Z	0.111	2.82
e	0.037 BSC	0.95 BSC
e1	0.075 BSC	1.90 BSC
b	0.032	0.80

Notes

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Pin 3 is the cathode (Unidirectional Only).
4. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM03P27M
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

No.1001, Shiwan (7) Road, Pudong District, Shanghai, P.R.China.201207

Tel: 86-21-68969993 Fax: 86-21-50757680 Email: market@way-on.com

WAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

WAYON® is registered trademark of Wayon Corporation.

Specifications are subject to change without notice.
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
Users should verify actual device performance in their specific applications.